

SOT223 PNP SILICON PLANAR HIGH PERFORMANCE TRANSISTOR

ISSUE 2 – FEBRUARY 1995

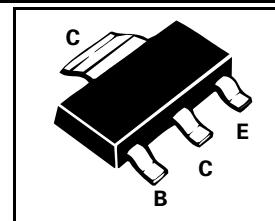
FZT751

FEATURES

- * 60 Volt V_{CEO}
- * 3 Amp continuous current
- * Low saturation voltage

COMPLEMENTARY TYPE – FZT651

PARTMARKING DETAIL – FZT751



ABSOLUTE MAXIMUM RATINGS.

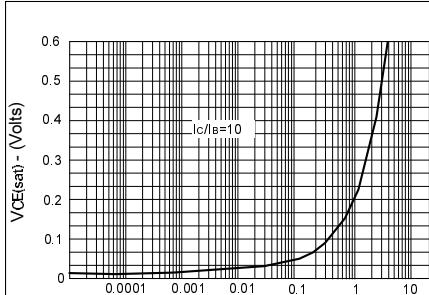
PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	-80	V
Collector-Emitter Voltage	V_{CEO}	-60	V
Emitter-Base Voltage	V_{EBO}	-5	V
Peak Pulse Current	I_{CM}	-6	A
Continuous Collector Current	I_C	-3	A
Power Dissipation at $T_{amb}=25^\circ\text{C}$	P_{tot}	2	W
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^\circ\text{C}$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-80			V	$I_C=100\mu\text{A}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-60			V	$I_C=10\text{mA}^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5			V	$I_E=100\mu\text{A}$
Collector Cut-Off Current	I_{CBO}			-0.1 -10	μA	$V_{CB}=-60\text{V}$ $V_{CB}=-60\text{V}, T_{amb}=100^\circ\text{C}$
Emitter Cut-Off Current	I_{EBO}			-0.1	μA	$V_{EB}=-4\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-0.15 -0.45	0.3 0.6	V	$I_C=1\text{A}, I_B=100\text{mA}^*$ $I_C=3\text{A}, I_B=300\text{mA}^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		-0.9	-1.25	V	$I_C=1\text{A}, I_B=100\text{mA}^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		-0.8	-1.0	V	$I_C=1\text{A}, V_{CE}=-2\text{V}^*$
Static Forward Current Transfer Ratio	h_{FE}	70 100 80 40	200 200 170 150	300		$I_C=50\text{mA}, V_{CE}=-2\text{V}^*$ $I_C=500\text{mA}, V_{CE}=-2\text{V}^*$ $I_C=1\text{A}, V_{CE}=-2\text{V}^*$ $I_C=2\text{A}, V_{CE}=-2\text{V}^*$
Transition Frequency	f_T	100	140		MHz	$I_C=100\text{mA}, V_{CE}=-5\text{V}$ $f=100\text{MHz}$
Switching Times	t_{on}		40		ns	$I_C=500\text{mA}, V_{CC}=-10\text{V}$
	t_{off}		450		ns	$I_B=I_{B2}=50\text{mA}$
Output Capacitance	C_{obo}			30	pF	$V_{CB}=-10\text{V}, f=1\text{MHz}$

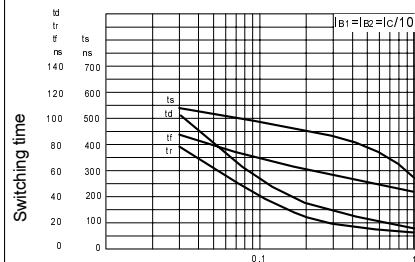
*Measured under pulsed conditions. Pulse width=300μs. Duty cycle ≤ 2%
Spice parameter data is available upon request for this device

TYPICAL CHARACTERISTICS



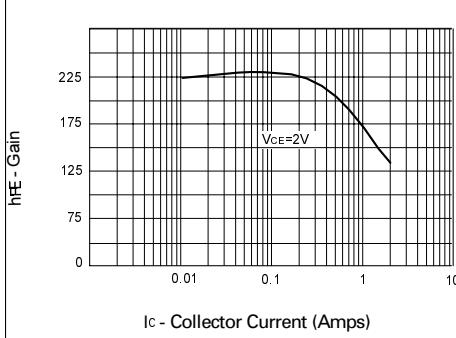
I_C - Collector Current (Amps)

$V_{CE(sat)}$ v I_C



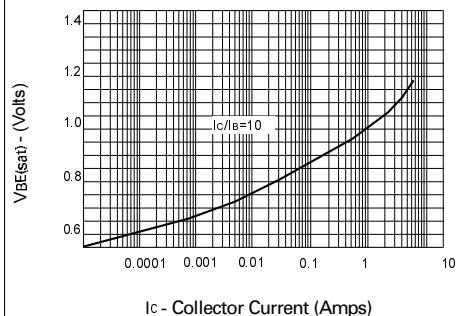
I_C - Collector Current (Amps)

Switching Speeds



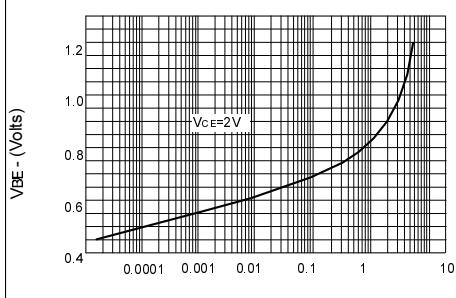
I_C - Collector Current (Amps)

h_{FE} v I_C



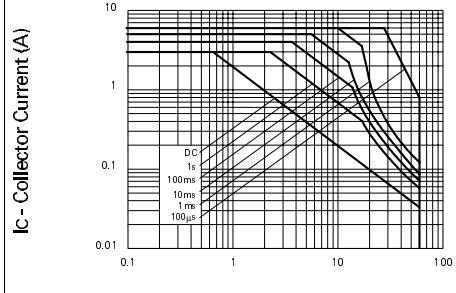
I_C - Collector Current (Amps)

$V_{BE(sat)}$ v I_C



I_C - Collector Current (Amps)

$V_{BE(on)}$ v I_C



V_{CE} - Collector Emitter Voltage (V)

Safe Operating Area